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SEMICONDUCTOR DEVICE AND
MANUFACTURING METHOD THEREOF

Abstract

PURPOSE: To enable the simultaneous burn-in of other good semiconductor chips in the wafer state even a defective semiconductor chip exists by series connecting a switch and second pad between a node and second common interconnection layer.

CONSTITUTION: A resistor circuit R11 is connected between a first common interconnection layer SLVDD and a node N11, a switch circuit SW11 between the nodes N11 and N13, and a second pad P12 between the layer SLVDD and node 14, respectively. The gates of N-channel MOS transistors Qn11 and Qn12 are connected between the layer SLVDD and a node N14, and first pad P11 between the nodes N11 and N14, respectively. The circuit SW11 has a fuse F11 connected between the nodes N11 and N12, a pad P13 between the nodes N12 and N13, and a pad 14 to the node N11, respectively.

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